

**REMARKS****Claim Rejections Under 35 U.S.C. § 102**

Claims 9, 13, 16-17 and 22 were rejected under 35 U.S.C. § 102(e) as being anticipated by Nagata (U.S. Patent No. 6,486,023). Applicant respectfully traverses this rejection.

Claims 9, 13, and 22 have been amended to more clearly claim the subject matter that Applicant regards as the invention. No new matter has been added since the additional limitations are taught in the specification at paragraphs 21 – 25 and in Figure 3.

Nagata discloses a memory device that has surface-channel peripheral transistors. The transistors, as disclosed in Figure 3 and described at col. 4, lines 47 – 51, are comprised of a gate 40 overlying a lightly p-doped channel region 42. The channel region 42 connects the source/drain regions 44, 46. The channel region 42 and source/drain regions 44, 46 are formed in an n-well 34 in a p-substrate 32 (see Figure 2). The Examiner is equating the n-well 34 of Nagata with Applicant's claimed lower well and the p-doped channel region 42 with Applicant's isolated upper well. Nagata, however, neither teaches nor suggests Applicant's invention as claimed.

It is well known in the art that a channel region has a different form and function from a well. The channel region 42 of Nagata is the region between the source and drain regions through which carriers are transported during operation of the transistor. Applicant's inner well, having a particular conductivity, isolates components within the well from components outside of the well. Therefore, the channel region 42 of Nagata is not the same thing as Applicant's inner well.

Additionally, Applicant claims a lower well having a first conductivity formed in a substrate having a second conductivity and an upper well formed within the first well. The upper well is doped to have the second conductivity. Thus, components formed in the upper well are isolated from components formed in other portions of the substrate. This structure is neither taught nor suggested by Nagata.

**Allowable Subject Matter**

Claims 10-11 and 14-15 were objected to as being dependent upon a rejected base claim, but would be allowable if rewritten in independent form, including all of the limitations of the base claim and any intervening claims. Claims 18-21 were allowed.

**RESPONSE TO NON-FINAL OFFICE ACTION**

Serial No. 10/681,414

Title: COMMON WORDLINE FLASH ARRAY ARCHITECTURE

**PAGE 6**

Attorney Docket No. 400.241US01

**CONCLUSION**

For the above-cited reasons, Applicant respectfully requests that the Examiner allow the claims of the present application. If the Examiner has any questions or concerns regarding this application, please contact the undersigned at (612) 312-2211. No new matter has been added and no additional fee is required by this amendment and response.

Respectfully submitted,

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Kenneth W. Bolvin

Kenneth W. Bolvin  
Reg. No. 34,125

Attorneys for Applicant  
Leffert Jay & Polglaze  
P.O. Box 581009  
Minneapolis, MN 55458-1009  
T 612 312-2200  
F 612 312-2250